L Number	Hits	Search Text	DB	Time stamp
-	6	(("5637884") or ("5811324")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/16 15:17
-	6	(("4979014") or ("5466621")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 14:38
-	382	(257/900).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 14:39
-	378	((257/900).CCLS.) and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/26 09:35
-	234007	(("257") or ("438")).CLAS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 14:44
-	682	(((257/$) or (438/$)).CCLS.) and @ad<=20000731 and 'convex' with 'layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 14:49
-	1	"5095347".PN.	USPAT	2002/05/07 14:46
-	1	"5095347".PN.	USPAT	2002/05/07 14:46
-	1	"5120666".PN.	USPAT	2002/05/07 14:46
-	1	"4774196".PN.	USPAT	2002/05/07 14:46
-	1	"5410172".PN.	USPAT	2002/05/07 14:47
-	1	"5420055".PN.	USPAT	2002/05/07 14:47
-	1	"5578513".PN.	USPAT	2002/05/07 14:47
-	1	"5580802".PN.	USPAT	2002/05/07 14:48
-	610	(((257/$) or (438/$)).CCLS.) and @ad<=20000731 and 'convex' with 'semiconductor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 14:51
-	0	(((257/$) or (438/$)).CCLS.) and @ad<=20000731 and 'convex semiconductor' and 'side-wall gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 14:52
-	0	(((257/$) or (438/$)).CCLS.) and @ad<=20000731 and 'convex semiconductor' and 'side wall gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 14:53
-	1531	(((257/$) or (438/$)).CCLS.) and @ad<=20000731 and 'side wall gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 14:57

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-	40	((((257/$) or (438/$)).CCLS.) and @ad<=20000731 and 'side wall gate') and 'convex'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 15:09
-	238	(257/394).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 15:12
-	232	(257/394).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 15:43
-	1	"4979014".PN.	USPAT	2002/05/07 15:30
-	1	"5463241".PN.	USPAT	2002/05/07 15:30
-	1	"5512770".PN.	USPAT	2002/05/07 15:31
-	156	(257/262).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 15:56
-	17	'trench isolated transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 15:57
-	17	trench adj isolated adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 16:39
-	1	"4449285".PN.	USPAT	2002/05/07 15:59
-	1	"4606011".PN.	USPAT	2002/05/07 15:59
-	1	"4670768".PN.	USPAT	2002/05/07 15:59
-	1	"4449285".PN.	USPAT	2002/05/07 16:09
-	1	"4606011".PN.	USPAT	2002/05/07 16:09
-	1	"4670768".PN.	USPAT	2002/05/07 16:09
-	1	"4801988".PN.	USPAT	2002/05/07 16:11
-	1	"4833516".PN.	USPAT	2002/05/07 16:11
-	1	"4910567".PN.	USPAT	2002/05/07 16:11
-	1	"5013679".PN.	USPAT	2002/05/07 16:12
-	1	"5013679".PN.	USPAT	2002/05/07 16:12
-	1	"5264716".PN.	USPAT	2002/05/07 16:12
-	1	"5289027".PN.	USPAT	2002/05/07 16:12
-	1	"5348905".PN.	USPAT	2002/05/07 16:13
-	1	"5360758".PN.	USPAT	2002/05/07 16:13
-	1	"5404037".PN.	USPAT	2002/05/07 16:13
-	1	"5567962".PN.	USPAT	2002/05/07 16:13
-	1	"5567962".PN.	USPAT	2002/05/07 16:13

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-	1	"5567962".PN.	USPAT	2002/05/07 16:14
-	1	"5675164".PN.	USPAT	2002/05/07 16:14
-	1	"5909044".PN.	USPAT	2002/05/07 16:15
-	1	"5990510".PN.	USPAT	2002/05/07 16:15
-	1	"5994197".PN.	USPAT	2002/05/07 16:15
-	1	"5994729".PN.	USPAT	2002/05/07 16:15
-	1	"5998820".PN.	USPAT	2002/05/07 16:16
-	1	"5998821".PN.	USPAT	2002/05/07 16:16
-	1	"6008513".PN.	USPAT	2002/05/07 16:16
-	1	"6020609".PN.	USPAT	2002/05/07 16:17
-	1	"6025620".PN.	USPAT	2002/05/07 16:17
-	1	"6037210".PN.	USPAT	2002/05/07 16:17
-	2781	side adj wall adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 16:26
-	46	(side adj wall adj gate) and @ad<=20000731 and 'convex'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 16:23
-	80	'side-wall' adj gates	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 16:27
-	77	('side-wall' adj gates) and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 16:43
-	24	'convex semiconductor layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 07:58
-	24	'convex semiconductor layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 16:38
-	1	"3278789".PN.	USPAT	2002/05/08 08:10
-	1	"3663857".PN.	USPAT	2002/05/08 08:10
-	1	"3735186".PN.	USPAT	2002/05/08 08:10
-	1	"4093562".PN.	USPAT	2002/05/08 08:10
-	1	"4325084".PN.	USPAT	2002/05/08 08:10
-	1	"5066883".PN.	USPAT	2002/05/08 08:11
-	1	"3805123".PN.	USPAT	2002/05/08 08:11
-	1	"5753966".PN.	USPAT	2002/05/08 08:11
-	1	"5753966".PN.	USPAT	2002/05/08 08:12

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-	1	"5814532".PN.	USPAT	2002/05/08 08:12
-	1	"5972730".PN.	USPAT	2002/05/08 08:12
-	1	"6037210".PN.	USPAT	2002/05/08 08:31
-	1	"6025620".PN.	USPAT	2002/05/08 08:31
-	1	"6020609".PN.	USPAT	2002/05/08 08:31
-	1	"5998821".PN.	USPAT	2002/05/08 08:31
-	155	'projection' near 'semiconductor substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 08:46
-	143	('projection' near 'semiconductor substrate') and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 09:54
-	799	(257/192).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:57
-	403	((257/192).ccls. and @ad<=20000731) and 'FET'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 10:00
-	201	(257/386).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 10:17
-	244	(257/387).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 10:26
-	111	(257/388).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 10:32
-	149	(257/389).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 10:37
-	259	(257/393).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 10:39
-	315	(257/346).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 10:43
-	93	(257/395).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 10:47
-	67	(257/27).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 10:49

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-	206	(257/69).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 10:54
-	39	(438/247).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 10:59
-	86	(438/159).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 11:01
-	177	(438/155).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 11:03
-	139	(257/348).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:16
-	173	'surrounding gate transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 16:01
-	1842	(257/296).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 10:31
-	4811	((257/296) or (257/306) or (257/530) or (257/354) or (438/238-239)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/26 09:44
-	542	((257/296).ccls. and @ad<=20000731) and 'surrounding gate transistor' or 'SGT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/26 09:42
-	166	'surrounding gate transistor' and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/11 06:07
-	87	'gate electrode' with 'electric field effect'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 09:59
-	275	'gate electrode applying'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 10:02
-	39	'gate electrode applying' with 'electric field'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 10:07
-	2	'gate electrode applying' with 'electric field' with 'channel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 10:10

-	87	'gate electrode applying' and 'electric field' and 'channel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 10:11
-	196	'surrounding gate transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 15:49
-	1	"4979014".PN.	USPAT	2003/02/26 09:03
-	1	"5019878".PN.	USPAT	2003/02/26 09:03
-	1	"5089870".PN.	USPAT	2003/02/26 09:04
-	1	"5115289".PN.	USPAT	2003/02/26 09:04
-	1	"5163180".PN.	USPAT	2003/02/26 09:06
-	2	("5424227").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/26 09:30
-	828	((257/192).CCLS.) and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/16 15:40
-	46	((257/196).CCLS.) and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/26 09:35
-	577	((257/296).ccls. and @ad<=20000731) and 'surrounding gate transistor' or 'SGT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/26 09:44
-	23	((257/296).ccls. and @ad<=20000731) and 'surrounding gate transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/26 09:44
-	5205	((257/296) or (257/306) or (257/530) or (257/354) or (438/238-239)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/26 09:49
-	4	(("5670810") or ("5414287")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/26 11:04
-	2	"20020011612"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/16 15:17
-	506	@ad<=20000731 and 'SGT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 08:06
-	174	@ad<=20000731 and surrounding adj1 gate adj1 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:42

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-	70	@ad<=20000731 and 'SGT' and (257/$).ccls. and (438/$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 08:07
-	1037	(257/401).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/11 07:42
-	43	(438/284).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 08:23
-	2	("20020011612").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 15:31
-	2	("5466621").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 15:31
-	178	@ad<=20000731 and 'surrounding gate transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:41
-	32	'convex semiconductor layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 16:40
-	687	'SGT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 16:41
-	55	@ad<=20000731 and 'sgt' and 'side wall'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/11 06:12
-	8	'surrounding gate transistor' and @ad<=20000731 and 'offset' with 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/11 06:07
-	180	@ad<=20000731 and 'surrounding gate transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/11 06:12
-	48	@ad<=20000731 and 'sgt' and 'offset'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/11 06:13
-	2	@ad<=20000731 and 'sgt' and 'offset' with 'sidewall'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/11 06:13
-	496	(257/328).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:20

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-	181	(257/263).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/11 07:43
-	367	(257/302).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:40
-	158	(257/348).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:16
-	166	(257/262).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:24
-	181	(257/263).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:24
-	1394	(257/347).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:41
-	83	@ad<=20000731 and 'surrounding' adj1 'channel' adj1 'region'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:42
-	180	@ad<=20000731 and surrounding adj1 gate adj1 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:42
-	395	(257/900).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 09:25
-	1050	(257/401).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 09:27
-	326	(257/618).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 09:45
-	296	(257/402).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 09:28

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